

November 1990

# 74FR16245 16-Bit Transceiver with TRI-STATE® Outputs

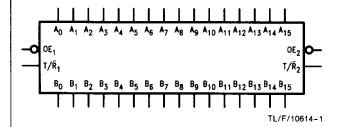
### **General Description**

The 'FR16245 contains sixteen non-inverting bidirectional buffers with TRI-STATE outputs and is intended for bus-oriented applications. Current sinking capability is 64 mA on both the A and B ports. The device is byte controlled. Each byte has separate control inputs which can be shorted together for full 16-bit operation. The transmit/receive  $(T/\overline{Rn})$  inputs determine the direction of data flow through the transceiver. The output enable  $(\overline{OEn})$  inputs disable both A and B ports by placing them in an high impedance state.

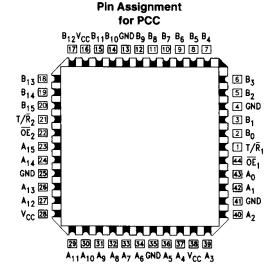
### **Features**

- Non-inverting buffers
- Bidirectional data paths
- A and B output sink capability of 64 mA, source capability of 15 mA
- Separate control pins for each byte
- Guaranteed 4000V minimum ESD protection
- Guaranteed pin to pin skew
- Low TRI-STATE IIL
- 16-Bit version of the 'F245 or 'F645

### **Logic Symbol**



### **Connection Diagram**



TL/F/10614-3

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## **Pin Descriptions**

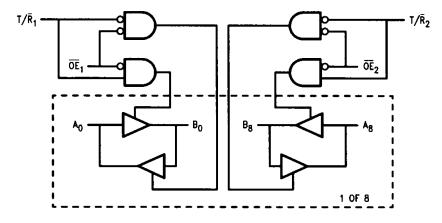
Pin Names	Description
ŌĒn	Output Enable Input
T/R <sub>n</sub>	Transmit/Receive Input
A <sub>0</sub> -A <sub>15</sub>	A Bus Inputs/
	TRI-STATE Outputs
B <sub>0</sub> -B <sub>15</sub>	B Bus Inputs/
	TRI-STATE Outputs

## **Truth Table**

	Inputs			Output Operating Mode				
Byte	1 (0:7)	(0:7) Byte2 (8:15)		Output Operating Mode				
ŌĒ <sub>1</sub>	T/R <sub>1</sub>	OE <sub>2</sub>	T/R <sub>2</sub>	Byte1 (0:7)	Byte2 (8:15)			
L	L	Н	X	Bus B Data to A	High Z State			
L	н	н	X	Bus A Data to B	High Z State			
Н	X	L	L	High Z State	Bus B Data to A			
H	X	L	Н	High Z State	Bus A Data to B			
L	L	L	L	Bus B Data to A	Bus B Data to A			
L	Н	L	н	Bus A Data to B	Bus A Data to B			
Н	X	H	X	High Z State	High Z State			

H = High Voltage Level
L = Low Voltage Level
X = Immaterial

## **Logic Diagram**



TL/F/10614-2

### **Absolute Maximum Ratings** (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature

-65°C to +150°C

Ambient Temperature under Bias

-55°C to +125°C -55°C to +175°C

Junction Temperature under Bias V<sub>CC</sub> Pin Potential to

**Ground Pin** 

-0.5V to +7.0V

Input Voltage (Note 2)

-0.5V to +7.0V

Input Current (Note 2)

-30 mA to  $\pm 5.0$  mA

Voltage Applied to Output

in HIGH State (with  $V_{CC} = 0V$ )

Standard Output TRI-STATE Output

 $-0.5\mbox{V to V}_{CC}$   $-0.5\mbox{V to } +5.5\mbox{V}$ 

Current Applied to Output

in LOW State (Max)

Twice the Rated IOL (mA)

ESD Last Passing Voltage (Min)

4000V

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

## Recommended Operating Conditions

Free Air Ambient Temperature

Commercial

0°C to +70°C

Supply Voltage

Commercial

+ 4.5 V to + 5.5 V

### **DC Electrical Characteristics**

Symbol Parameter	Parameter	74FR			Units	V	Conditions	
	raiametei	Min	Тур	Max	Oilles	V <sub>CC</sub>	Conditions	
V <sub>IH</sub>	Input HIGH Voltage	2.0			v		Recognized as a HIGH Signal	
V <sub>IL</sub>	Input LOW Voltage			0.8	٧	:	Recognized as a LOW Signal	
V <sub>CD</sub>	Input Clamp Diode Voltage			-1.2	٧	Min	$I_{IN} = -18 \text{ mA}$	
V <sub>OH</sub>	Output HIGH Voltage	2.4 2.0	2.8 2.44		٧	Min	$I_{OH} = -3 \text{ mA}$ $I_{OH} = -15 \text{ mA}$ $(A_n, B_n)$	
V <sub>OL</sub>	Output LOW Voltage		0.45	0.55	v	Min	I <sub>OL</sub> = 64 mA (A <sub>n</sub> , B <sub>n</sub> )	
Ін	Input HIGH Current			5.0	μΑ	Max	$V_{IN} = 2.7V$	
I <sub>BVI</sub>	Input HIGH Current Break- Down Test			7.0	μΑ	Max	$V_{IN} = 7.0V$ $(\overline{OE}_n, T/\overline{R}_n)$	
I <sub>BVIT</sub>	Input HIGH Current Breakdown Test (I/O)			0.1	mA	Max	$V_{IN} = 5.5V$ $(A_n, B_n)$	
ارر	Input LOW Current			-150 -100	μA μA	Max Max	$V_{IN} = 0.5V (T/\overline{R}_n, A_n, B_n)$ $V_{IN} = 0.5V (\overline{OE}_n)$	

## DC Electrical Characteristics (Continued)

Symbol Paramet	Parameter	74FR			Unit	V	Conditions	
- Syllibol	Parameter	Min	Тур	Max		V <sub>CC</sub>	Conditions	
los	Output Short- Circuit Current	-100		225	mA	Max	$V_{OUT} = 0V$ $(A_n, B_n)$	
l <sub>IH</sub> +	Output Leakage Current		0	25	μΑ	Max	$V_{OUT} = 2.7V$ (A <sub>n</sub> , B <sub>n</sub> )	
l <sub>IL</sub> + lozl	Output Leakage Current		-20	-150	μΑ	Max	V <sub>OUT</sub> = 0.5V (A <sub>n</sub> , B <sub>n</sub> )	
l <sub>CEX</sub>	Output High Leakage Current			50	μΑ	Max	$V_{OUT} = V_{CC}$ (A <sub>n</sub> , B <sub>n</sub> )	
V <sub>ID</sub>	Input Leakage Test	4.75			V	0.0	$I_{\text{ID}} = 1.9 \mu\text{A}$ All Other Pins Grounded	
lod ————————————————————————————————————	Output Circuit Leakage Current			3.75	μΑ	0.0	V <sub>IOD</sub> = 150 mV All Other Pins Grounded	
l <sub>ZZ</sub>	Bus Drainage Test			100	μΑ	0.0	$V_{OUT} = 5.25V$ (A <sub>n</sub> , B <sub>n</sub> )	
Іссн	Power Supply Current		70	105	mA	Max	V <sub>O</sub> = HIGH	
ICCL	Power Supply Current		127	165	mA	Max	V <sub>O</sub> = LOW	
lccz	Power Supply Current		71	105	mA	Max	V <sub>O</sub> = HIGH Z	
C <sub>IN</sub>	Input Capacitance		8.0		pF	5.0	ŌĒ, T/R	
			17.0		pF	5.0	A <sub>n</sub> , B <sub>n</sub>	

## **AC Electrical Characteristics**

Symbol Paramet			74FR		74	FR	
	Parameter		T <sub>A</sub> = +25°( V <sub>CC</sub> = +5.0 C <sub>L</sub> = 50 pF	V	T <sub>A</sub> , V <sub>CC</sub> = Comm V <sub>CC</sub> = Comm C <sub>L</sub> = 50 pF		Unit
		Min	Тур	Max	Min	Max	]
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay A <sub>n</sub> to B <sub>n</sub> or B <sub>n</sub> to A <sub>n</sub>	1.3 1.3	2.7 2.2	4.3 4.3	1.3 1.3	4.3 4.3	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time	3.9 3.9	6.9 9.7	13.9 13.9	3.9 3.9	13.9 13.9	ns
t <sub>PHZ</sub>	Output Disable Time	1.8 1.8	3.9 4.4	6.3 6.3	1.8 1.8	6.3 6.3	ns

## **Extended AC Characteristics**

Symbol Parameter	74	FR	74	FR	Unit	
	Parameter	V <sub>CC</sub> = C <sub>L</sub> = 16 Ou Swite	Comm Comm 50 pF utputs ching te 2)	T <sub>A</sub> = Comm V <sub>CC</sub> = Comm C <sub>L</sub> = 250 pF (Note 3)		
		Min	Max	Min	Max	1
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay  An to Bn or Bn to An	1.3 1.3	5.8 5.8	3.2 3.2	8.2 8.2	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time	3.9 3.9	14.6 14.6			ns
t <sub>PHZ</sub>	Output Disable Time	1.8 1.8	6.3 6.3	-		ns
t <sub>OSHL</sub> (Note 1)	Pin to Pin Skew for HL Transitions		TBD			ns
<sup>t</sup> OSLH (Note 1)	Pin to Pin Skew for LH Transitions		TBD	-		ns
t <sub>OST</sub> (Note 1)	Pin to Pin Skew for HL/LH Transitions		TBD			ns

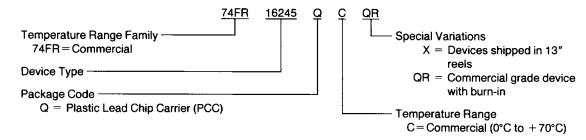
Note 1: Skew is defined as the absolute value of the difference between the actual propagation delays for any two outputs of the same device. The specification applies to any outputs switching HIGH to LOW (t<sub>OSHL</sub>) LOW to HIGH (t<sub>OSLH</sub>), or any combination of HIGH to LOW and/or LOW to HIGH (t<sub>OST</sub>).

Note 2: This specification is guaranteed but not tested The limits apply to propagation delays for all paths described switching in phase, i.e., all LOW-to-HIGH, HIGH-to-LOW, TRI-STATE-to-HIGH, etc.

Note 3: These specifications guaranteed but not tested. The limits represent propagation delays with 250 pF load capacitors in place of the 50 pF load capacitors in the standard AC load. This specification pertains to single output switching only.

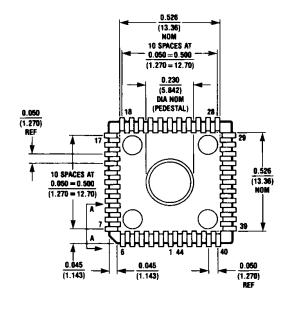
### **Ordering Information**

The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:

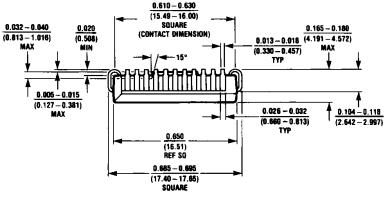


### Physical Dimensions inches (millimeters)









V44A (REV H)

44-Lead Plastic Chip Carrier (Q)
NS Package Number V44A

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